

Average gate power dissipation ($T_j=125$)	$P_{G(AV)}$	0.5	W
Peak gate power	P_{GM}	10	W
Peak pulse voltage ($T_j=25$; non-repetitive, off-state; FIG.7)	V_{pp}	2.5	kV

ELECTRICAL CHARACTERISTICS ($T_j=25$ unless otherwise specified)

Symbol	Test Condition	Quadrant	Value		Unit
I_{GT}	$V_D=12V$ $R_L=33$	- -	MAX.	50	mA
V_{GT}		- -	MAX.	1	V
V_{GD}	$V_D=V_{DRM}$ $T_j=125$ $R_L=3.3k$	- -	MIN.	0.2	V
I_L	$I_G=1.2I_{GT}$	-	MAX.	50	mA
				90	

ORDERING INFORMATION

	J	ST	08	F	-800	BW
JieJie Microelectronics Co., Ltd.		Triacs	$I_{T(RMS)}:8A$			
			$F:TO-220F(Ins)$			$BW:I_{GT1-3} 50mA$
					$800:V_{DRM}/V_{RRM} 800V$	

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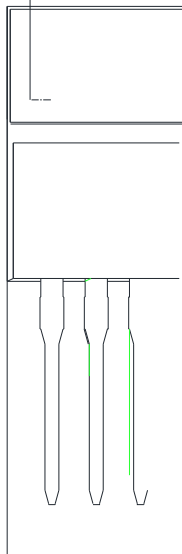
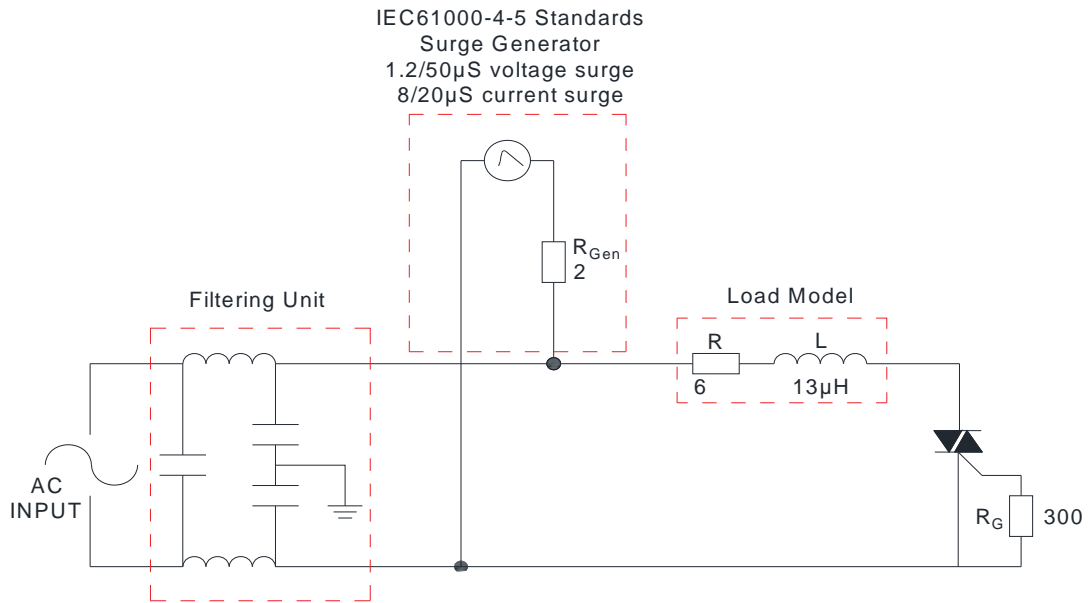



FIG.7 Test circuit for inductive and resistive loads to IEC-61000-4-5 standards



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